Please amend 25 as follows:

SUB D1 B1

25. (Amended) A semiconductor substrate comprising:

an n-th patterned mask containing a material having a growth suppressing effect, provided on or above a lower substrate, wherein n is an integer of 1 or more;

an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-th mask;

an (n+1)-th patterned mask containing a material having a growth suppressing material substantially provided above an opening of the n-th patterned mask; and

an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask.

Please add the following new claims 27-36:

SUB D2 B2

27. (New) A semiconductor substrate comprising:

an n-th patterned mask containing a material having a growth suppressing effect, provided on or above a lower substrate, wherein n is an integer of 1 or more;

an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-th mask;

an (n+1)-th patterned mask containing a material having a growth suppressing effect, provided so as to be at an angle relative to the n-th patterned mask; and

an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1) n-th patterned mask.

28. (New) A light-emitting device produced by using the semiconductor substrate of claim 27.

29. (New) A light-emitting device according to claim 26, including a cladding layer of AlGaN made of a mixed crystal semiconductor material containing four elements and a trace amount of another element.

30. (New) A light-emitting device according to claim 26, including a quantum-well layer or a barrier layer each of which is made of a mixed crystal semiconductor material containing four or more elements including a mixed crystal containing the three elements of InGaN and a trace amount of another element.

31. (New) A light-emitting device according to claim 26, including a stripe-shaped ridge structure which is positioned about 3 μm or more away from both ends of a mesa structure which is provided to form an n-type electrode.

32. (New) A light-emitting device according to claim 26, including an n-type electrode formed on the back plane of the substrate having n-type conducting and a stripe-shaped ridge structure which is positioned about 3 μm or more away from both ends of the device.

33. (New) A light-emitting device according to claim 28, including a cladding layer of AlGaN made of a mixed crystal semiconductor material containing four elements and a trace amount of another element.

B2 cont

34. (New) A light-emitting device according to claim 28, including a quantum-well layer or a barrier layer each of which is made of a mixed crystal semiconductor material containing four or more elements including a mixed crystal containing the three elements of InGaN and a trace amount of another element.